2N3467
2N3468

SILICON
PNP TRANSISTORS

TO-39 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3467 and 2N3468 are silicon PNP switching transistors designed for core driver applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**	**2N3467**	**2N3468**	**UNITS**
Collector-Base Voltage	V_{CBO}	40	50	V
Collector-Emitter Voltage	V_{CEO}	40	50	V
Emitter-Base Voltage	V_{EBO}	5.0		V
Continuous Collector Current	I_C	1.0		A
Power Dissipation	P_D	1.0		W
Power Dissipation (T_C=25°C)	P_D	5.0		W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200		°C
Thermal Resistance	Θ_{JA}	175		°C/W
Thermal Resistance	Θ_{JC}	35		°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

		2N3467		**2N3468**		
SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**MIN**	**MAX**	**UNITS**
I_{CBO}	V_{CB}=30V	-	100	-	100	nA
I_{CBO}	V_{CB}=30V, T_A=100°C	-	15	-	15	μA
I_{CEV}	V_{CE}=30V, V_{BE}=3.0V	-	100	-	100	nA
I_{BEV}	V_{CE}=30V, V_{BE}=3.0V	-	120	-	120	nA
BV_{CBO}	I_C=10μA	40	-	50	-	V
BV_{CEO}	I_C=10mA	40	-	50	-	V
BV_{EBO}	I_E=10μA	5.0	-	5.0	-	V
$V_{CE(SAT)}$	I_C=150mA, I_B=15mA	-	0.3	-	0.36	V
$V_{CE(SAT)}$	I_C=500mA, I_B=50mA	-	0.5	-	0.6	V
$V_{CE(SAT)}$	I_C=1.0A, I_B=100mA	-	1.0	-	1.2	V
$V_{BE(SAT)}$	I_C=150mA, I_B=15mA	-	1.0	-	1.0	V
$V_{BE(SAT)}$	I_C=500mA, I_B=50mA	0.8	1.2	0.8	1.2	V
$V_{BE(SAT)}$	I_C=1.0A, I_B=100mA	-	1.6	-	1.6	V
h_{FE}	V_{CE}=1.0V, I_C=150mA	40	-	25	-	
h_{FE}	V_{CE}=1.0V, I_C=500mA	40	120	25	75	
h_{FE}	V_{CE}=5.0V, I_C=1.0A	40	-	20	-	

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ELECTRICAL CHARACTERISTICS - Continued: (T_A=25°C unless otherwise noted)

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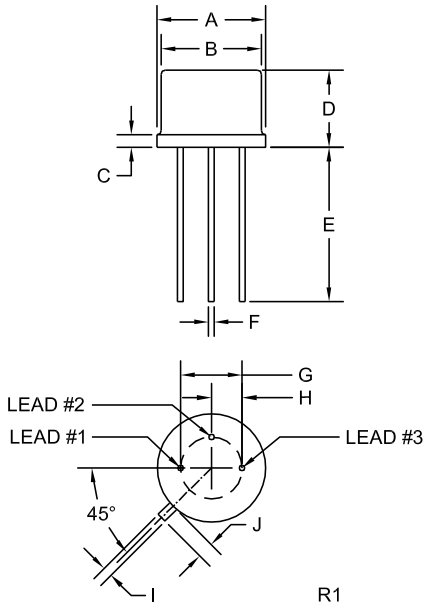
SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**MIN**	**MAX**	**UNITS**
f_T	V_{CE}=10V, I_C=50mA, f=100MHz	175	-	150	-	MHz
C_{ob}	V_{CB}=10V, I_E=0, f=100kHz	-	25	-	25	pF
C_{ib}	V_{EB}=0.5V, I_C=0, f=100kHz	-	100	-	100	pF
t_{on}	V_{CC}=30V, V_{BE}=2.0V, I_C=500mA, I_{B1}=50mA	-	40	-	40	ns
t_{off}	V_{CC}=30V, I_C=500mA, I_{B1}=I_{B2}=50mA	-	90	-	90	ns
Q_T	V_{CC}=30V, I_C=500mA, I_B=50mA	-	6.0	-	6.0	nC

TO-39 CASE - MECHANICAL OUTLINE



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

LEAD CODE:
1) Emitter
2) Base
3) Collector

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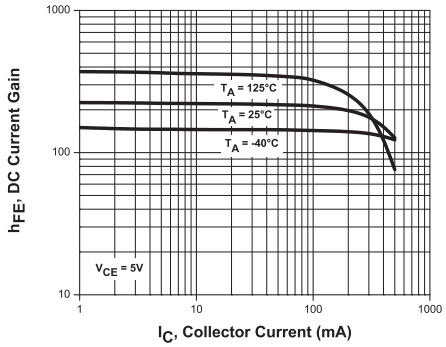
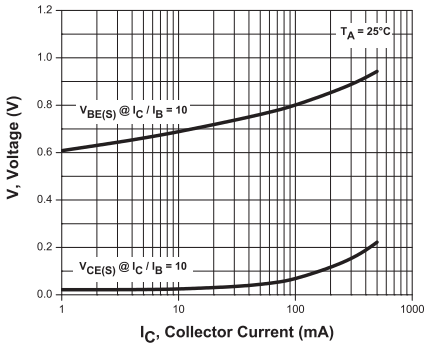
TYPICAL ELECTRICAL CHARACTERISTICS

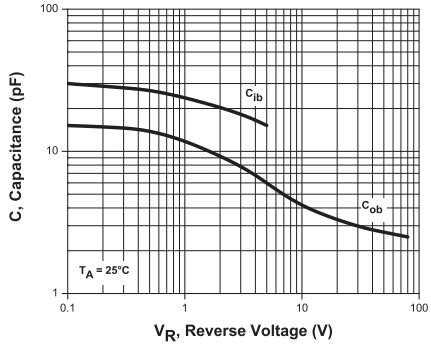
DC Current Gain



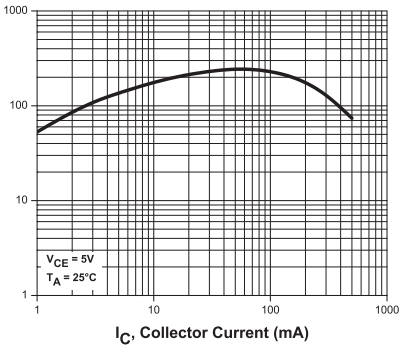
"ON" Voltage



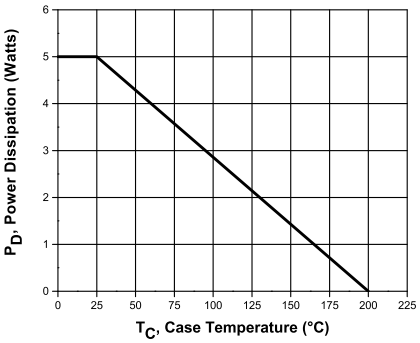
Capacitance



Current Gain-Bandwidth Product



Power Derating



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